

PMEM4020APD

PNP transistor/Schottky rectifier module

Rev. 02 — 31 August 2009

Product data sheet

1. Product profile

1.1 General description

Combination of a PNP transistor with low V_{CEsat} and high current capability and a planar Schottky barrier rectifier with an integrated guard ring for stress protection in a SOT457 (SC-74) small plastic package. NPN complement: PMEM4020AND

1.2 Features

- 600 mW total power dissipation
- High current capability up to 2 A
- Reduces printed-circuit board area required
- Reduces pick and place costs
- Small plastic SMD package
- Transistor
 - ◆ Low collector-emitter saturation voltage
- Diode
 - ◆ Ultra high-speed switching
 - ◆ Very low forward voltage
 - ◆ Guard ring protected

1.3 Applications

- DC-to-DC converters
- Inductive load drivers
- General purpose load drivers
- Reverse polarity protection circuits
- MOSFET drivers

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
PNP transistor						
V_{CEO}	collector-emitter voltage	open base	-	-	-40	V
I_C	collector current (DC)	continuous; $T_s \leq 55\text{ °C}$	[1] -	-	-2	A

Table 1. Quick reference data ...continued

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Schottky barrier rectifier						
V_R	continuous reverse voltage		-	-	40	V
I_F	continuous forward current		-	-	1	A

[1] Soldering point of collector or cathode tab.

2. Pinning information

Table 2. Discrete pinning

Pin	Description	Simplified outline	Symbol
1	emitter		<p style="text-align: right;"><i>sym040</i></p>
2	not connected		
3	cathode		
4	anode		
5	base		
6	collector		

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PMEM4020APD	SC-74	plastic surface mounted package; 6 leads	SOT457

4. Marking

Table 4. Marking

Type number	Marking code
PMEM4020APD	D3

5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
PNP transistor					
V_{CBO}	collector-base voltage	open emitter	-	-40	V
V_{CEO}	collector-emitter voltage	open base	-	-40	V
V_{EBO}	emitter-base voltage	open collector	-	-5	V

Table 5. Limiting values ...continued

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
I_C	collector current (DC)	continuous	[1] -	-0.75	A
		continuous	[2] -	-1	A
		continuous	[3] -	-1.3	A
		continuous; $T_s \leq 55\text{ °C}$	[4] -	-2	A
I_{CM}	peak collector current		-	-3	A
I_{BM}	peak base current		-	-1	A
P_{tot}	total power dissipation	$T_{amb} \leq 25\text{ °C}$	[1] -	295	mW
		$T_{amb} \leq 25\text{ °C}$	[2] -	400	mW
		$T_{amb} \leq 25\text{ °C}$	[3] -	500	mW
		$T_s \leq 55\text{ °C}$	[4] -	1000	mW
T_j	junction temperature		-	150	°C
Schottky barrier rectifier					
V_R	continuous reverse voltage		-	40	V
I_F	continuous forward current		-	1	A
I_{FRM}	repetitive peak forward current	$t_p \leq 1\text{ ms}; \delta \leq 0.5$	-	3.5	A
I_{FSM}	non-repetitive peak forward current	$t = 8\text{ ms};$ square wave	-	10	A
P_{tot}	total power dissipation	$T_{amb} \leq 25\text{ °C}$	[1] -	295	mW
		$T_{amb} \leq 25\text{ °C}$	[2] -	400	mW
		$T_{amb} \leq 25\text{ °C}$	[3] -	500	mW
		$T_s \leq 55\text{ °C}$	[4] -	1000	mW
T_j	junction temperature		[2] -	150	°C
Combined device					
P_{tot}	total power dissipation	$T_{amb} \leq 25\text{ °C}$	[2] -	600	mW
T_{stg}	storage temperature		-65	+150	°C
T_{amb}	ambient temperature		[2] -65	+150	°C

[1] Mounted on a FR4 printed-circuit board, single-sided copper, tin-plated, standard footprint.

[2] Device mounted on a printed-circuit board, single-sided copper, tin-plated, 1 cm² mounting pad for both collector and cathode.

[3] Mounted on a ceramic printed-circuit board, single-sided copper, tin-plated, standard footprint.

[4] Soldering point of collector or cathode tab.

6. Thermal characteristics

Table 6. Thermal characteristics^[1]

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Single device						
$R_{th(j-s)}$	thermal resistance from junction to soldering point	in free air	^[2] -	-	95	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	^[3] -	-	250	K/W
			^[4] -	-	315	K/W
			^[5] -	-	425	K/W
Combined device						
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	^[3] -	-	208	K/W

[1] For Schottky barrier rectifiers thermal run-away has to be considered, as in some applications the reverse power losses P_R are a significant part of the total power losses. Nomograms for determining the reverse power losses P_R and $I_{F(AV)}$ rating will be available on request.

[2] Soldering point of collector or cathode tab.

[3] Mounted on a ceramic printed-circuit board, single-sided copper, tin-plated, standard footprint.

[4] Device mounted on a printed-circuit board, single-sided copper, tin-plated, 1 cm² mounting pad for both collector and cathode tab.

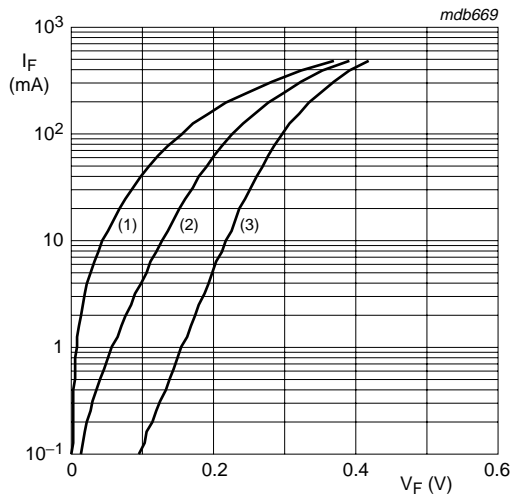
[5] Mounted on a FR4 printed-circuit board, single-sided copper, tin-plated, standard footprint.

7. Characteristics

Table 7. Characteristics
T_{amb} = 25 °C unless otherwise specified

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
PNP transistor						
I _{CBO}	collector-base cut-off current	V _{CB} = -40 V; I _E = 0 A	-	-	-100	nA
		V _{CB} = -40 V; I _E = 0 A; T _j = 150 °C	-	-	-50	μA
I _{CEO}	collector-emitter cut-off current	V _{CE} = -30 V; I _B = 0 A	-	-	-100	nA
I _{EBO}	emitter-base cut-off current	V _{EB} = -5 V; I _C = 0 A	-	-	-100	nA
h _{FE}	DC current gain	V _{CE} = -5 V; I _C = -1 mA	300	-	-	
		V _{CE} = -5 V; I _C = -100 mA	300	-	-	
		V _{CE} = -5 V; I _C = -500 mA	250	-	900	
		V _{CE} = -5 V; I _C = -1 A	160	-	-	
		V _{CE} = -5 V; I _C = -2 A	[1] 50	-	-	
V _{CEsat}	collector-emitter saturation voltage	I _C = -100 mA; I _B = -1 mA	-	-	-120	mV
		I _C = -500 mA; I _B = -50 mA	-	-	-145	mV
		I _C = -1 A; I _B = -100 mA	-	-	-260	mV
		I _C = -2 A; I _B = -200 mA	-	-	-530	mV
R _{CEsat}	equivalent on-resistance	I _C = -1 A; I _B = -100 mA	[1] -	180	280	mΩ
V _{BEsat}	base-emitter saturation voltage	I _C = -1 A; I _B = -100 mA	[1] -	-	-1.1	V
V _{BEon}	base-emitter turn-on voltage	V _{CE} = -5 V; I _C = -1 A	[1] -	-	-1.0	V
f _T	transition frequency	V _{CE} = -10 V; I _C = -50 mA; f = 100 MHz	150	-	-	MHz
C _c	collector capacitance	V _{CB} = -10 V; I _E = I _e = 0 A; f = 1 MHz	-	-	10	pF
Schottky barrier rectifier						
V _F	continuous forward voltage	see Figure 1				
		I _F = 0.1 mA	[1] -	95	130	mV
		I _F = 1 mA	[1] -	155	210	mV
		I _F = 10 mA	[1] -	220	270	mV
		I _F = 100 mA	[1] -	295	350	mV
I _R	reverse current	see Figure 2				
		V _R = 10 V	[1] -	7	20	μA
		V _R = 40 V	[1] -	30	100	μA
C _d	diode capacitance	V _R = 1 V; f = 1 MHz; see Figure 3	-	43	48	pF

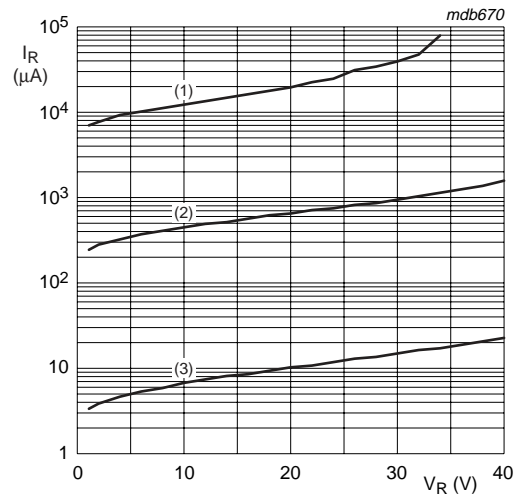
[1] Pulse test: t_p ≤ 300 μs; δ ≤ 0.02



Schottky barrier rectifier

- (1) $T_{amb} = 150\text{ °C}$
- (2) $T_{amb} = 85\text{ °C}$
- (3) $T_{amb} = 25\text{ °C}$

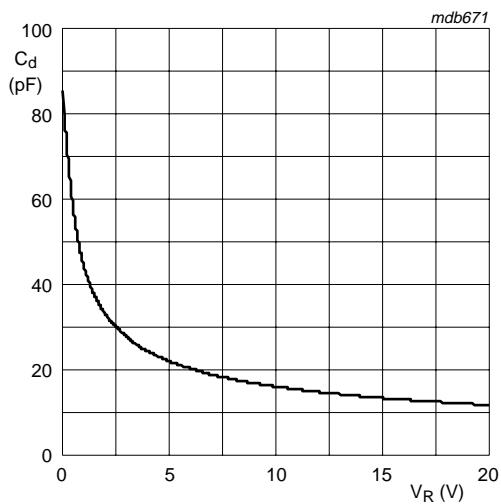
Fig 1. Forward current as a function of forward voltage; typical values



Schottky barrier rectifier

- (1) $T_{amb} = 150\text{ °C}$
- (2) $T_{amb} = 85\text{ °C}$
- (3) $T_{amb} = 25\text{ °C}$

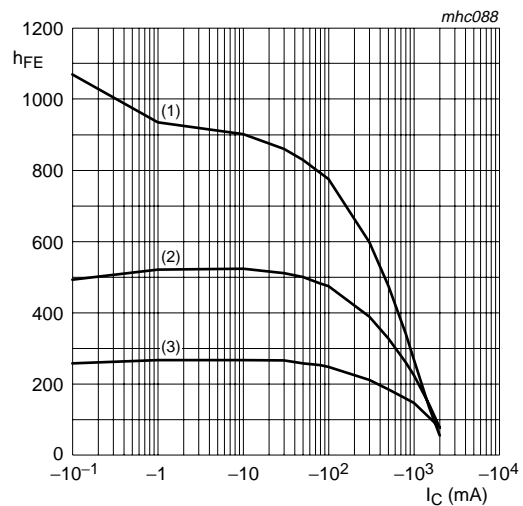
Fig 2. Reverse current as a function of reverse voltage; typical values



Schottky barrier rectifier;

$T_{amb} = 25\text{ °C}; f = 1\text{ MHz}$

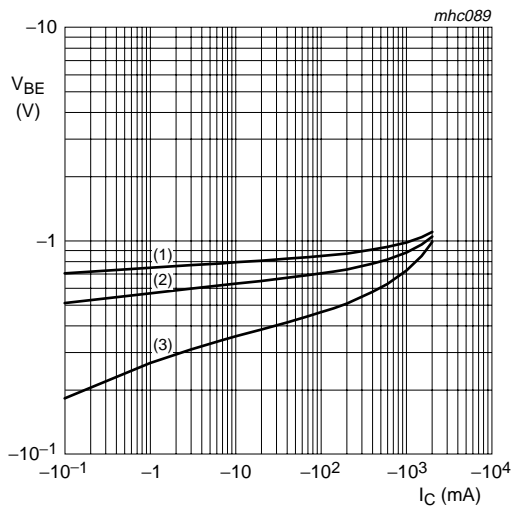
Fig 3. Diode capacitance as a function of reverse voltage; typical values



PNP transistor; $V_{CE} = -5\text{ V}$

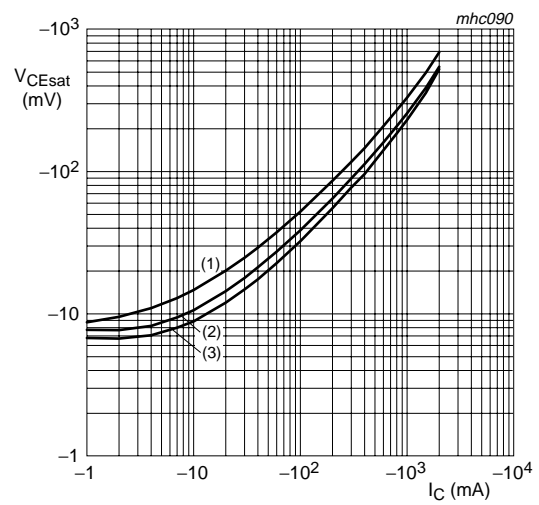
- (1) $T_{amb} = 150\text{ °C}$
- (2) $T_{amb} = 25\text{ °C}$
- (3) $T_{amb} = -55\text{ °C}$

Fig 4. DC current gain as a function of collector current; typical values



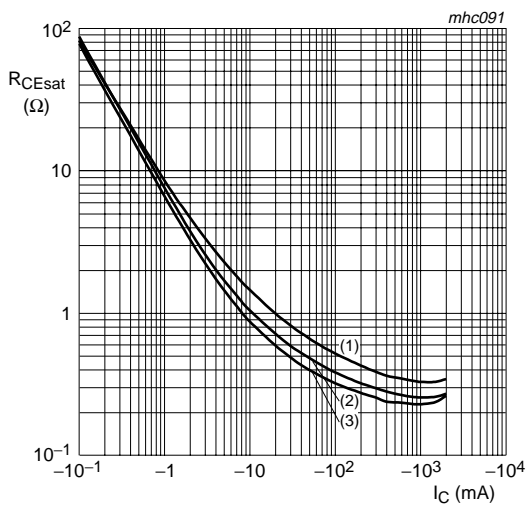
PNP transistor; $V_{CE} = -5\text{ V}$
 (1) $T_{amb} = -55\text{ °C}$
 (2) $T_{amb} = 25\text{ °C}$
 (3) $T_{amb} = 150\text{ °C}$

Fig 5. Base-emitter voltage as a function of collector current; typical values



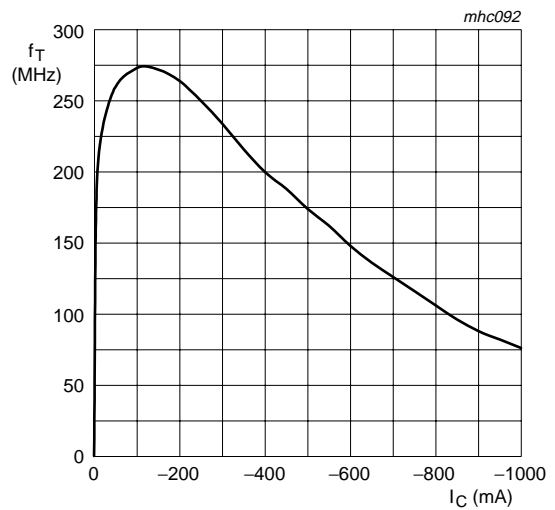
PNP transistor; $I_C/I_B = 10$
 (1) $T_{amb} = 150\text{ °C}$
 (2) $T_{amb} = 25\text{ °C}$
 (3) $T_{amb} = -55\text{ °C}$

Fig 6. Collector-emitter saturation voltage as a function of collector current; typical values



PNP transistor; $I_C/I_B = 10$
 (1) $T_{amb} = 150\text{ °C}$
 (2) $T_{amb} = 25\text{ °C}$
 (3) $T_{amb} = -55\text{ °C}$

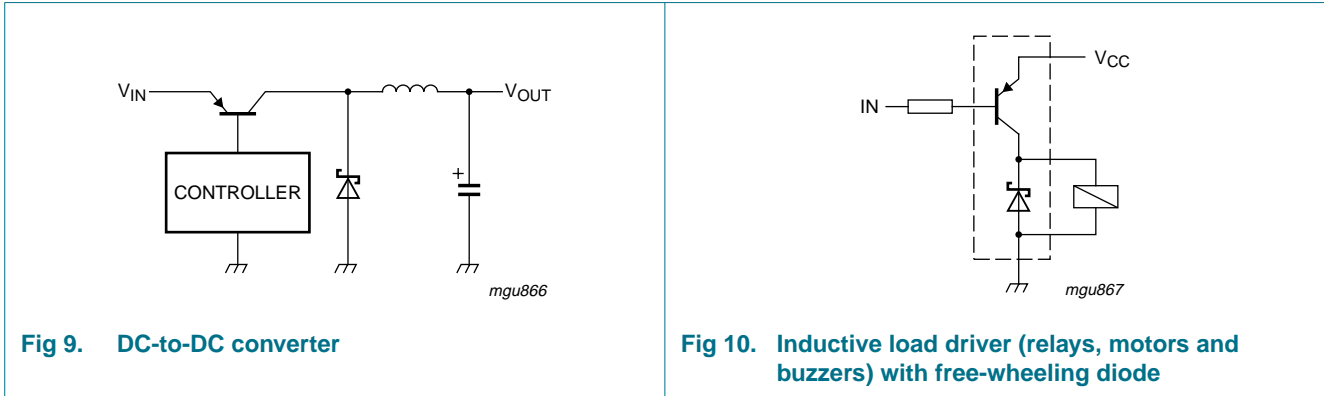
Fig 7. Equivalent on-resistance as a function of collector current; typical values



PNP transistor; $V_{CE} = -10\text{ V}$

Fig 8. Transition frequency as a function of collector current

8. Application information



9. Package outline

Plastic surface-mounted package (TSOP6); 6 leads

SOT457

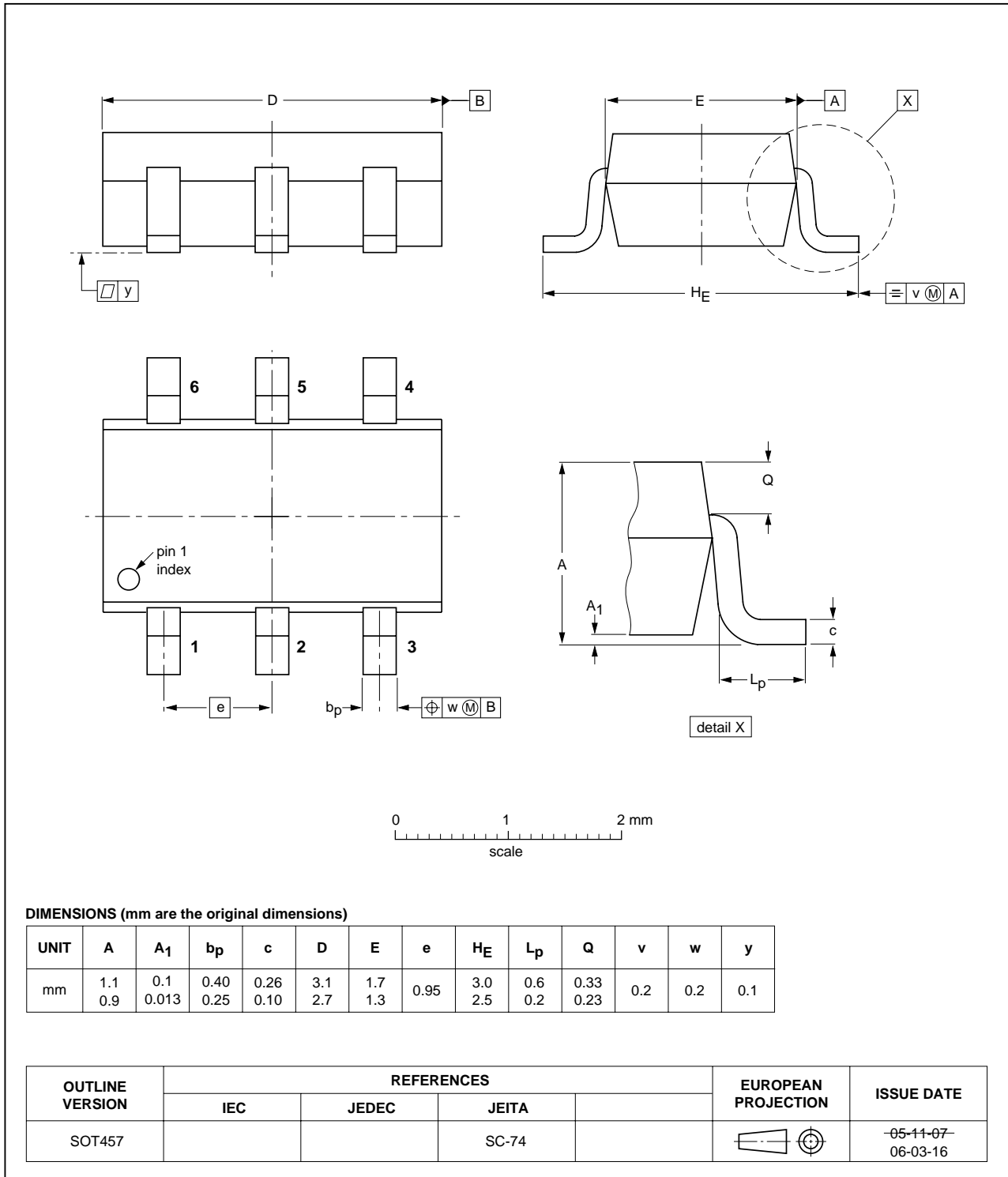


Fig 11. Package outline SOT457 (SC-74)

10. Packing information

Table 8. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.^[1]

Type number	Package	Description	Packing quantity	
			3000	10000
PMEM4020APD	SOT457	4 mm pitch, 8 mm tape and reel; T1	-115	-135
		4 mm pitch, 8 mm tape and reel; T2	-125	-165

[1] For further information and the availability of packing methods, see [Section 13](#).

11. Revision history

Table 9. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PMEM4020APD_2	20090831	Product data sheet	-	PMEM4020APD_1
Modifications:	<ul style="list-style-type: none">• This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content.• Table 2 “Discrete pinning”: amended• Figure 11 “Package outline SOT457 (SC-74)”: updated			
PMEM4020APD_1	20041004	Product data sheet	-	-

12. Legal information

12.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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